# DMG9640N

### Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

#### For digital circuits DMG5640N in SSMini6 type package

#### Features

- $\bullet$  High forward current transfer ratio  $h_{FE}$
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)
- Marking Symbol: S8

#### Basic Part Number

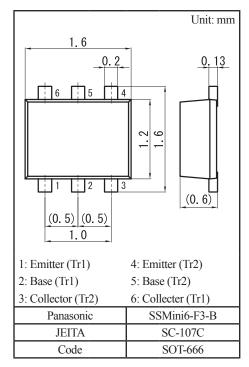
DRC2143Z + DRA2143Z (Individual)

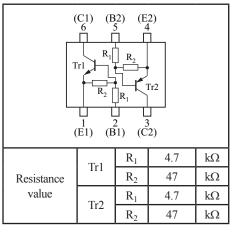
#### Packaging

DMG9640N0R Embossed type (Thermo-compression sealing): 8 000 pcs / reel (standard)

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter		Symbol	Rating	Unit	
Tr1	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
	Collector current	I <sub>C</sub>	100	mA	
Tr2	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
	Collector current	I <sub>C</sub>	-100	mA	
Overall	Total power dissipation	P <sub>T</sub>	125	mW	
	Junction temperature	Tj	150	°C	
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C	





### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2  {\rm mA},  I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{\rm EB} = 6  \rm V,  I_{\rm C} = 0$			0.2	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	80		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{\rm CE} = 0.2$ V, $I_{\rm C} = 5$ mA	1.3			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = 5 \text{ V}, I_C = 100 \mu\text{A}$			0.4	V
Input resistance	R <sub>1</sub>		-30%	4.7	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.08	0.10	0.12	_

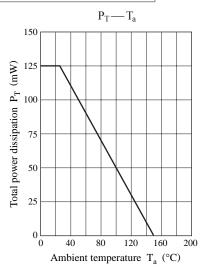
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2
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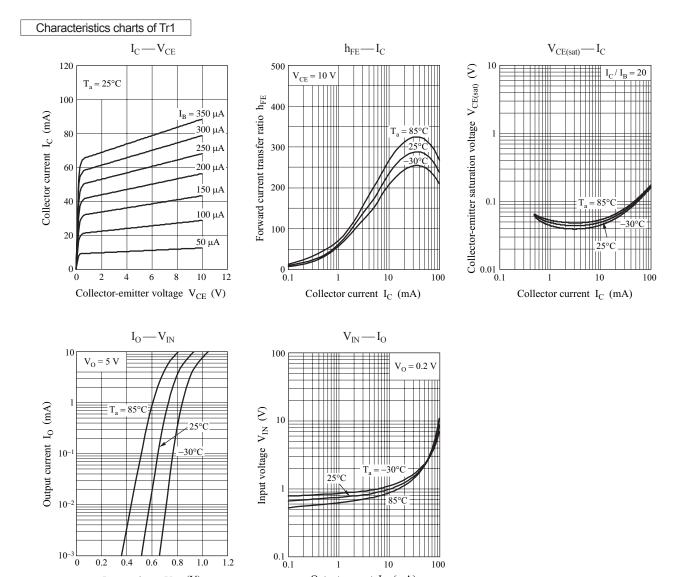
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2  {\rm mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			-0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -6 \text{ V}, I_C = 0$			- 0.2	mA
Forward current transfer ratio	$h_{\rm FE}$	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{CE} = -0.2 \text{ V}, I_C = -5 \text{ mA}$	-1.3			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = -5 V, I_C = -100 \mu A$			- 0.4	V
Input resistance	R <sub>1</sub>		-30%	4.7	+30%	kΩ
Resistance ratio	$R_1 / R_2$		0.08	0.10	0.12	

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart



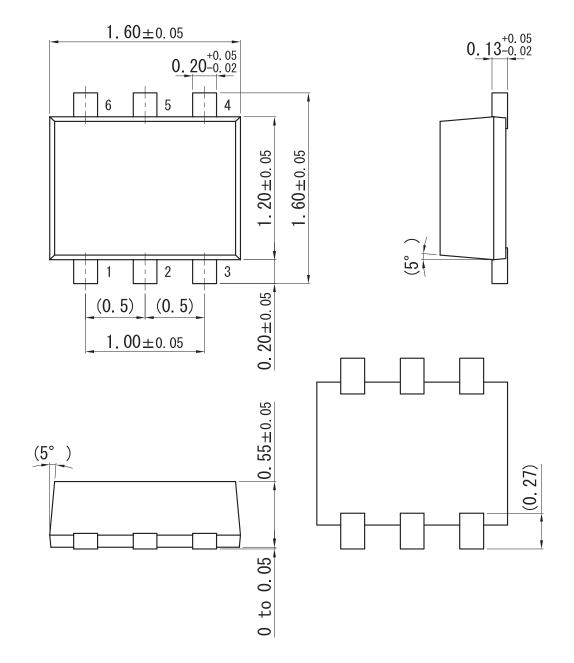
Input voltage  $V_{IN}$  (V)



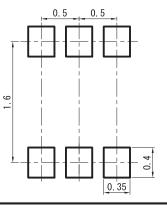
Output current I<sub>O</sub> (mA)

## SSMini6-F3-B

Unit: mm



Land Pattern (Reference) (Unit: mm)



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